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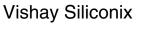
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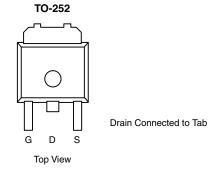
N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^a			
30	0.0120 at V _{GS} = 10 V	17.5			
30	$0.0175 \text{ at V}_{GS} = 4.5 \text{ V}$	14.5			

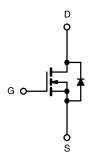
FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: SUD50N03-12P-E3 (Lead (PB) free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	30	V			
Gate-Source Voltage	V _{GS}	± 20	□			
Continuos Duris Commuta	T _A = 25 °C	I_	17.5			
Continuous Drain Current ^a	T _A = 100 °C	I _D	12.4			
Pulsed Drain Current	I _{DM}	40	Α			
Continuous Source Current (Diode Conduction) ^a	I _S	5				
Avalanche Current	L = 0.1 mH	I _{AS}	30	7		
Single Pulse Avalanche Energy	L=0.1 IIII	E _{AS}	45	mJ		
Maximum Dawar Dissination	T _C = 25 °C	В	46.8	w		
Maximum Power Dissipation	T _A = 25 °C	P _D	6.5 ^a] vv		
Operating Junction and Storage Temperature Range	•	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manifestore Investigate to Amelicanta	t ≤ 10 s	- R _{thJA}	18	23	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		40	50		
Maximum Junction-to-Case		R_{thJC}	2.6	3.2		

a. Surface mounted on FR4 board, $t \le 10 \text{ s.}$

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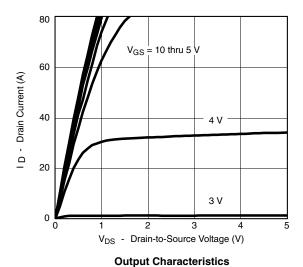
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min .	Typ. ^a	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V_{DS} $V_{GS} = 0 \text{ V, } I_{D} = 250 \mu\text{A}$				V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	1	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$			50	μΑ
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	40			Α
		V _{GS} = 10 V, I _D = 20 A		0.0100	0.0120	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C			0.0170	Ω
		V _{GS} = 4.5 V, I _D = 15 A		0.0138	0.0175	
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A	15			S
Dynamic ^a						
Input Capacitance	C _{iss}			1600		pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		285		
Reverse Transfer Capacitance	C _{rss}			140		
Total Gate Charge ^c	Q_{g}			28	42	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		6		nC
Gate-Drain Charge ^c	Q_{gd}			5		
Gate Resistance	R_{g}	f = 1 MHz	0.3	1.5	3.0	Ω
Turn-On Delay Time ^c	t _{d(on)}			9	15	
Rise Time ^c	t _r	$V_{DD} = 15 \text{ V}, R_{L} = 0.3 \Omega$		15	25	20
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		20	30	ns
Fall Time ^c	t _f			12	20	
Source-Drain Diode Ratings and Characteristics ($T_C = 25 ^{\circ}C$)						
Pulsed Current	I _{SM}				100	Α
Diode Forward Voltage ^b	V_{SD}	I _F = 40 A, V _{GS} = 0 V		1.2	1.5	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 50 A, dl/dt = 100 A/μs		25	70	ns

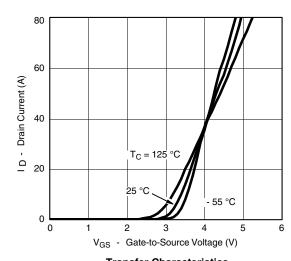
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C unless noted)

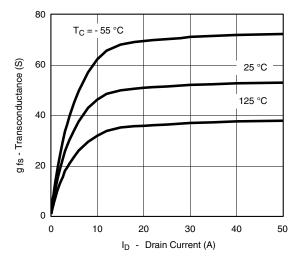




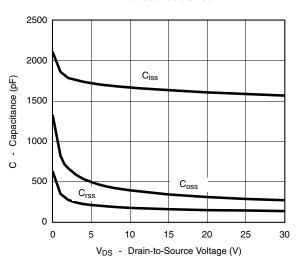
Transfer Characteristics



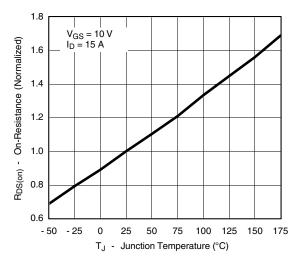
TYPICAL CHARACTERISTICS (25 °C unless noted)



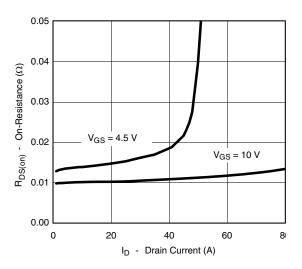
Transconductance



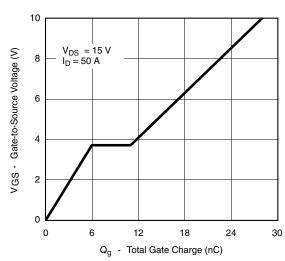
Capacitance



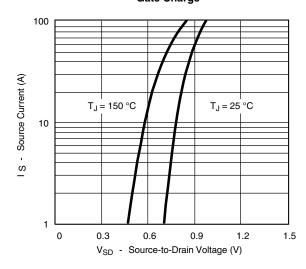
On-Resistance vs. Junction Temperature



On-Resistance vs. Drain Current



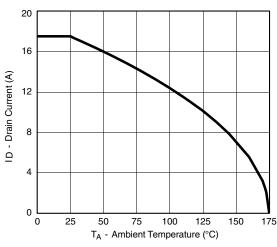
Gate Charge

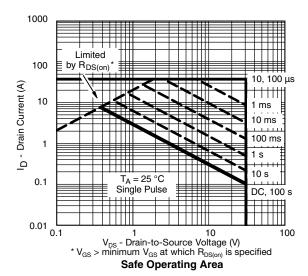


Source-Drain Diode Forward Voltage

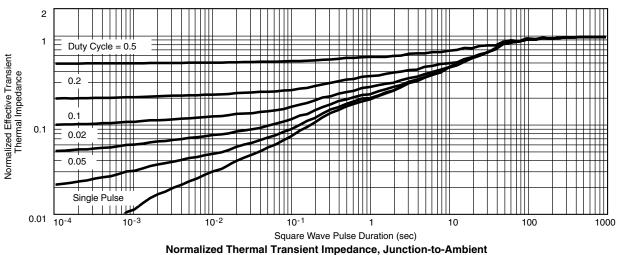
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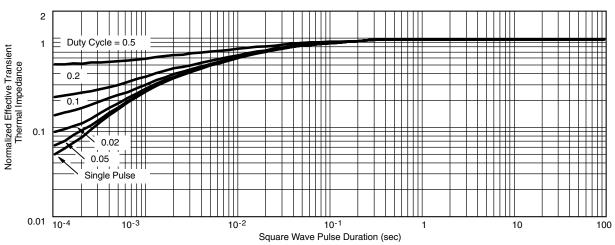
THERMAL RATINGS





Maximum Drain Current vs. Ambient Temperature



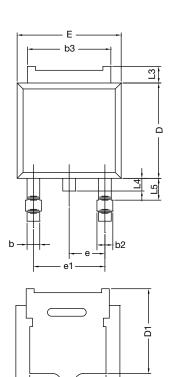


Normalized Thermal Transient Impedance, Junction-to-Case

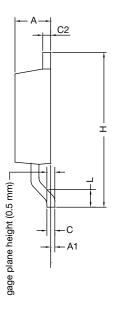
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72267.



TO-252AA CASE OUTLINE



E1



	MILLIMETERS		INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC 0.09		0 BSC	
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12					

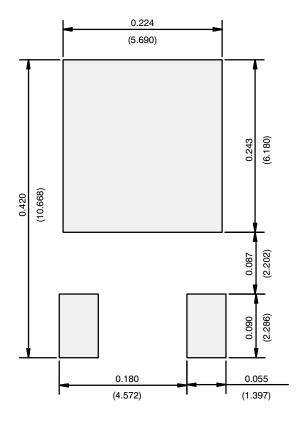
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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Revision: 02-Oct-12 Document Number: 91000